Bipolar Power Transistors

NPN Silicon

Features

- Epoxy Meets UL 94, V-0 @ 0.125 in
- ESD Ratings:
 - Human Body Model, 3B; > 8000 V
 - ♦ Machine Model, C; > 400 V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V _{CB}	40	Vdc
Emitter-Base Voltage	V _{EB}	6.0	Vdc
Base Current - Continuous	I _B	1.0	Adc
Collector Current Continuous Peak	lc	3.0 5.0	Adc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Power Dissipation Total P_D @ T_A = 25°C (Note 1) Total P_D @ T_A = 25°C (Note 2)	P _D	2.0 0.80	W
Thermal Resistance, Junction-to-Case Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	$R_{ heta JA} \ R_{ heta JA}$	64 155	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	TL	260	°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	–55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

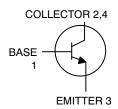
- Mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material.
 Mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material.



ON Semiconductor®

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NPN TRANSISTOR 3.0 AMPERES 40 VOLTS, 2.0 WATTS







CASE 318E STYLE 1



= Assembly Location

Year

W = Work Week

4031N = Specific Device Code = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]		
NJT4031NT1G	SOT-223	1000 / Tape &		
NJV4031NT1G	(Pb-Free)	Reel		
NJT4031NT3G	SOT-223	4000 / Tape &		
NJV4031NT3G	(Pb-Free)	Reel		

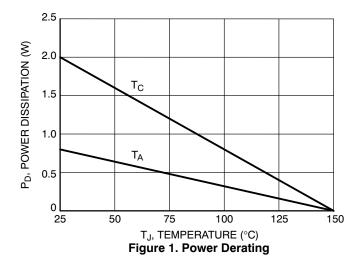
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	·				
Collector–Emitter Sustaining Voltage (I _C = 10 mAdc, I _B = 0 Adc)	V _{CEO(sus)}	40	_	_	Vdc
Emitter–Base Voltage ($I_E = 50 \mu Adc$, $I_C = 0 Adc$)	V _{EBO}	6.0	_	_	Vdc
Collector Cutoff Current (V _{CB} = 40 Vdc)	I _{CBO}	-	_	100	nAdc
Emitter Cutoff Current (V _{BE} = 6.0 Vdc)	I _{EBO}	-	-	100	nAdc
ON CHARACTERISTICS (Note 3)	,				
Collector–Emitter Saturation Voltage ($I_C = 0.5 \text{ Adc}$, $I_B = 5.0 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}$, $I_B = 10 \text{ mAdc}$) ($I_C = 3.0 \text{ Adc}$, $I_B = 0.3 \text{ Adc}$)	V _{CE(sat)}	- - -	- - -	0.100 0.150 0.300	Vdc
Base–Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.1 Adc)	V _{BE(sat)}	-	-	1.0	Vdc
Base–Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 2.0 Vdc)	V _{BE(on)}	-	-	1.0	Vdc
DC Current Gain $(I_C = 0.5 \text{ Adc}, V_{CE} = 1.0 \text{ Vdc})$ $(I_C = 1.0 \text{ Adc}, V_{CE} = 1.0 \text{ Vdc})$ $(I_C = 3.0 \text{ Adc}, V_{CE} = 1.0 \text{ Vdc})$	h _{FE}	220 200 100	- - -	500	
DYNAMIC CHARACTERISTICS					
Output Capacitance (V _{CB} = 10 Vdc, f = 1.0 MHz)	C _{ob}	-	25	-	pF
Input Capacitance (V _{EB} = 5.0 Vdc, f = 1.0 MHz)	C _{ib}	-	170	-	pF
Current–Gain – Bandwidth Product (Note 4) (I _C = 500 mA, V _{CE} = 10 V, F _{test} = 1.0 MHz)	f⊤	_	215	_	MHz

^{3.} Pulse Test: Pulse Width $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2\%.$

^{4.} $f_T = |h_{FE}| \bullet f_{test}$



TYPICAL CHARACTERISTICS

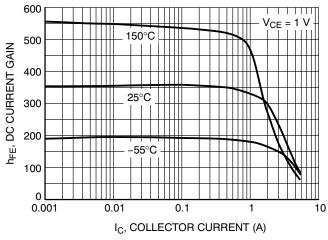


Figure 2. DC Current Gain

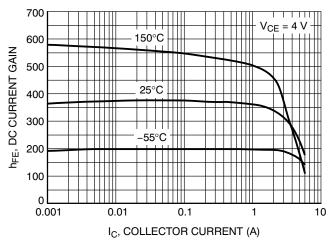


Figure 3. DC Current Gain

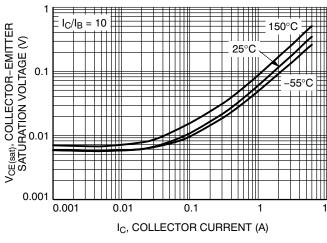


Figure 4. Collector-Emitter Saturation Voltage

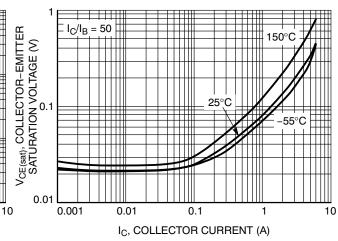


Figure 5. Collector-Emitter Saturation Voltage

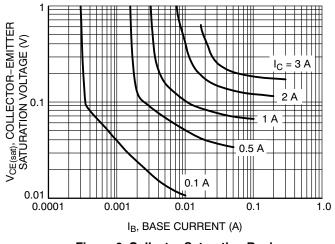


Figure 6. Collector Saturation Region

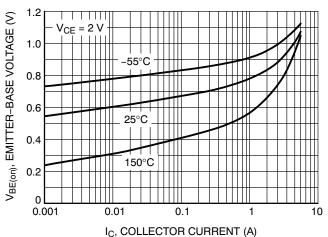


Figure 7. V_{BE(on)} Voltage

TYPICAL CHARACTERISTICS

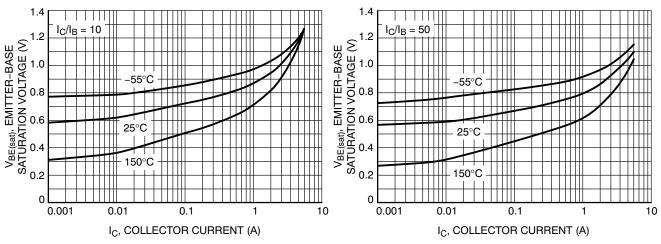


Figure 8. Base-Emitter Saturation Voltage

Figure 9. Base-Emitter Saturation Voltage

 $T_J = 25^{\circ}C$

f_{test} = 1 MHz

70

80

90

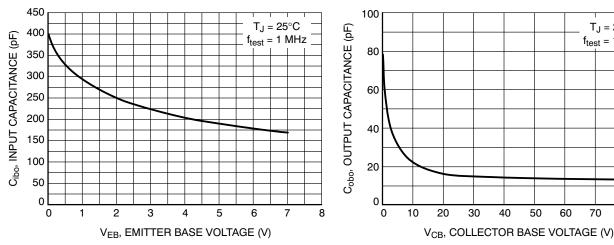


Figure 10. Input Capacitance

Figure 11. Output Capacitance

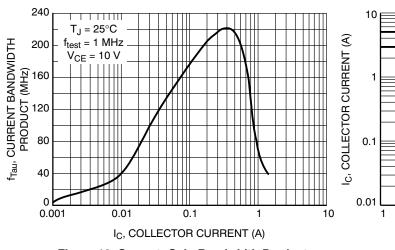


Figure 12. Current-Gain Bandwidth Product

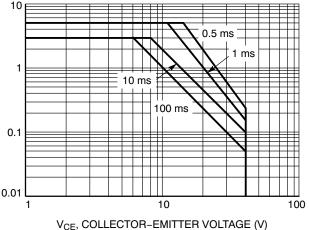
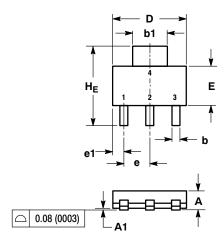


Figure 13. Safe Operating Area

PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE N





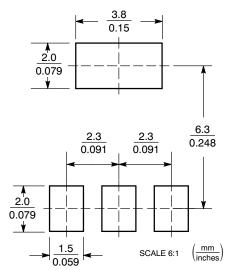
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
С	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
е	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20		-	0.008		_
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°

STYLE 1: PIN 1. BASE

- COLLECTOR EMITTER 2. 3.
- COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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